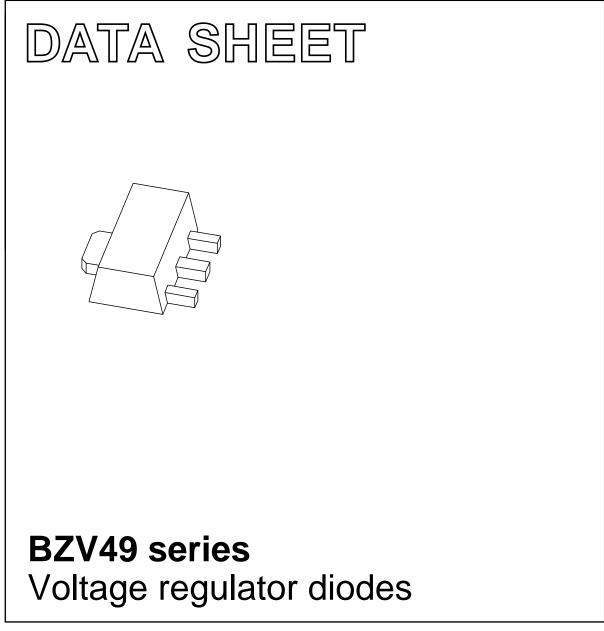
## DISCRETE SEMICONDUCTORS



Product specification Supersedes data of 1999 May 11 2005 Feb 03



**Semiconductors** 

**Philips** 

## **BZV49** series

#### FEATURES

- Total power dissipation: max. 1 W
- Tolerance series: approx. ±5%
- Working voltage range: nom. 2.4 to 75 V (E24 range)
- Non-repetitive peak reverse power dissipation: max. 40 W.

#### **APPLICATIONS**

• General regulation functions.

#### DESCRIPTION

Medium-power voltage regulator diodes in a SOT89 plastic SMD package.

The diodes are available in the normalized E24 approx.  $\pm 5\%$  tolerance range. The series consists of 37 types with nominal working voltages from 2.4 to 75 V (BZV49-C2V4 to BZV49-C75).

#### PINNING

PIN	DESCRIPTION
1	anode
2	cathode
3	anode

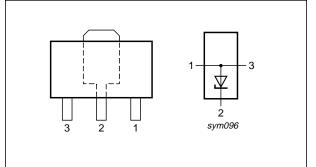


Fig.1 Simplified outline (SOT89) and symbol.

#### ORDERING INFORMATION

TYPE NUMBER		PACKAGE						
ITPE NUMBER	NAME	DESCRIPTION	VERSION					
BZV49-C2V4 to BZV49-C75 note 1	SC-62	plastic surface mounted package; collector pad for good heat transfer; 3 leads	SOT89					

#### Note

1. The series consists of 37 types with nominal working voltages from 2.4 to 75 V (E24 range).

#### MARKING

TYPE NUMBER	MARKING CODE	TYPE NUMBER	MARKING CODE	TYPE NUMBER	MARKING CODE	TYPE NUMBER	MARKING CODE
BZV49-C2V4	2Y4	BZV49-C6V2	6Y2	BZV49-C16	16Y	BZV49-C43	43Y
BZV49-C2V7	2Y7	BZV49-C6V8	6Y8	BZV49-C18	18Y	BZV49-C47	47Y
BZV49-C3V0	3Y0	BZV49-C7V5	7Y5	BZV49-C20	20Y	BZV49-C51	51Y
BZV49-C3Y3	3Y3	BZV49-C8V2	8Y2	BZV49-C22	22Y	BZV49-C56	56Y
BZV49-C3V6	3Y6	BZV49-C9V1	9Y1	BZV49-C24	24Y	BZV49-C62	62Y
BZV49-C3V9	3Y9	BZV49-C10	10Y	BZV49-C27	27Y	BZV49-C68	68Y
BZV49-C4V3	4Y3	BZV49-C11	11Y	BZV49-C30	30Y	BZV49-C75	75Y
BZV49-C4V7	4Y7	BZV49-C12	12Y	BZV49-C33	33Y	-	-
BZV49-C5V1	5Y1	BZV49-C13	13Y	BZV49-C36	36Y	-	-
BZV49-C5V6	5Y6	BZV49-C15	15Y	BZV49-C39	39Y	-	_

## **BZV49** series

#### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I <sub>F</sub>	continuous forward current		_	250	mA
I <sub>ZSM</sub>	non-repetitive peak reverse current	$t_p = 100 \ \mu s$ ; square wave; $T_j = 25 \ ^{\circ}C$ prior to surge	see Table "Per type		
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C; note 1	-	1	W
P <sub>ZSM</sub>	non-repetitive peak reverse power dissipation	wer $t_p = 100 \ \mu s$ ; square wave; $T_j = 25 \ ^\circ C$ prior to surge; see Fig.2		40	W
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C

#### Note

1. Device mounted on a ceramic substrate; area =  $2.5 \text{ cm}^2$ ; thickness = 0.7 mm.

#### **ELECTRICAL CHARACTERISTICS**

#### Total series

 $T_{amb}$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 50 mA; see Fig.3	1	V

N	Per	f۱
0		.,

BZV49- CXXX	VOL V <sub>Z</sub>	WORKING VOLTAGE V <sub>Z</sub> (V) at I <sub>Ztest</sub>		DLTAGE RESISTANCE $V_Z(V)$ $r_{dif}(\Omega)$		STANCE <sub>if</sub> (Ω)	TEMP. COEFF. S <sub>Z</sub> (mV/K) at I <sub>Ztest</sub> see Figs 4 and 5		TEST CURRENT I <sub>Ztest</sub> (mA)	DIODE CAP. $C_d (pF)$ at f = 1 MHz; at V <sub>R</sub> = 0 V	REVERSE CURRENT at REVERSE VOLTAGE		NON-REPETITIVE PEAK REVERSE CURRENT $I_{ZSM}$ (A) at t <sub>p</sub> = 100 µs;
			l						I <sub>R</sub> (μΑ)	VR	T <sub>amb</sub> = 25 °C		
	MIN.	MAX.	TYP.	MAX.	MIN.	TYP.	MAX.		MAX.	MAX.	(V)	MAX.	
2V4	2.2	2.6	70	100	-3.5	-1.6	0	5	450	50	1.0	6.0	
2V7	2.5	2.9	75	100	-3.5	-2.0	0	5	450	20	1.0	6.0	
3V0	2.8	3.2	80	95	-3.5	-2.1	0	5	450	10	1.0	6.0	
3V3	3.1	3.5	85	95	-3.5	-2.4	0	5	450	5	1.0	6.0	
3V6	3.4	3.8	85	90	-3.5	-2.4	0	5	450	5	1.0	6.0	
3V9	3.7	4.1	85	90	-3.5	-2.5	0	5	450	3	1.0	6.0	
4V3	4.0	4.6	80	90	-3.5	-2.5	0	5	450	3	1.0	6.0	
4V7	4.4	5.0	50	80	-3.5	-1.4	+0.2	5	300	3	2.0	6.0	
5V1	4.8	5.4	40	60	-2.7	-0.8	+1.2	5	300	2	2.0	6.0	
5V6	5.2	6.0	15	40	-2.0	+1.2	+2.5	5	300	1	2.0	6.0	
6V2	5.8	6.6	6	10	0.4	2.3	3.7	5	200	3	4.0	6.0	
6V8	6.4	7.2	6	15	1.2	3.0	4.5	5	200	2	4.0	6.0	
7V5	7.0	7.9	6	15	2.5	4.0	5.3	5	150	1	5.0	4.0	
8V2	7.7	8.7	6	15	3.2	4.6	6.2	5	150	0.7	5.0	4.0	
9V1	8.5	9.6	6	15	3.8	5.5	7.0	5	150	0.5	6.0	3.0	
10	9.4	10.6	8	20	4.5	6.4	8.0	5	90	0.2	7.0	3.0	
11	10.4	11.6	10	20	5.4	7.4	9.0	5	85	0.1	8.0	2.5	
12	11.4	12.7	10	25	6.0	8.4	10.0	5	85	0.1	8.0	2.5	
13	12.4	14.1	10	30	7.0	9.4	11.0	5	80	0.1	8.0	2.5	
15	13.8	15.6	10	30	9.2	11.4	13.0	5	75	0.05	10.5	2.0	
16	15.3	17.1	10	40	10.4	12.4	14.0	5	75	0.05	11.2	1.5	
18	16.8	19.1	10	45	12.4	14.4	16.0	5	70	0.05	12.6	1.5	
20	18.8	21.2	15	55	14.4	16.4	18.0	5	60	0.05	14.0	1.5	
22	20.8	23.3	20	55	16.4	18.4	20.0	5	60	0.05	15.4	1.25	
24	22.8	25.6	25	70	18.4	20.4	22.0	5	55	0.05	16.8	1.25	

Philips Semiconductors

Voltage regulator diodes

Product specification

BZV49 series

BZV49- CXXX	VOL V <sub>Z</sub>	WORKING VOLTAGE DIFFERENTIAL RESISTANCE   Vz (V) rdif (\Omega)   at Iztest at Iztest		TEMP. COEFF. S <sub>Z</sub> (mV/K) at I <sub>Ztest</sub> see Figs 4 and 5		TEST CURRENT I <sub>Ztest</sub> (mA)	DIODE CAP. $C_d$ (pF) at f = 1 MHz; at V <sub>R</sub> = 0 V	REVERSE CURRENT at REVERSE VOLTAGE		NON-REPETITIVE PEAK REVERSE CURRENT $I_{ZSM}$ (A) at $t_p = 100 \ \mu s;$		
										I <sub>R</sub> (μΑ)	VR	T <sub>amb</sub> = 25 °C
	MIN.	MAX.	TYP.	MAX.	MIN.	TYP.	MAX.		MAX.	MAX.	(V)	MAX.
27	25.1	28.9	25	80	21.4	23.4	25.3	2	50	0.05	18.9	1.0
30	28.0	32.0	30	80	24.4	26.6	29.4	2	50	0.05	21.0	1.0
33	31.0	35.0	35	80	27.4	29.7	33.4	2	45	0.05	23.1	0.9
36	34.0	38.0	35	90	30.4	33.0	37.4	2	45	0.05	25.2	0.8
39	37.0	41.0	40	130	33.4	36.4	41.2	2	45	0.05	27.3	0.7
43	40.0	46.0	45	150	37.6	41.2	46.6	2	40	0.05	30.1	0.6
47	44.0	50.0	50	170	42.0	46.1	51.8	2	40	0.05	32.9	0.5
51	48.0	54.0	60	180	46.6	51.0	57.2	2	40	0.05	35.7	0.4
56	52.0	60.0	70	200	52.2	57.0	63.8	2	40	0.05	39.2	0.3
62	58.0	66.0	80	215	58.8	64.4	71.6	2	35	0.05	43.4	0.3
68	64.0	72.0	90	240	65.6	71.7	79.8	2	35	0.05	47.6	0.25
75	70.0	79.0	95	255	73.4	80.2	88.6	2	35	0.05	52.5	0.2

2005 Feb 03

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# Product specification

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Voltage regulator diodes

BZV49 series

**BZV49** series

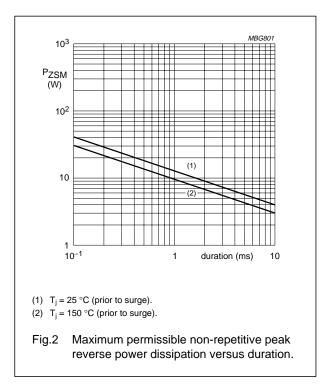
#### THERMAL CHARACTERISTICS

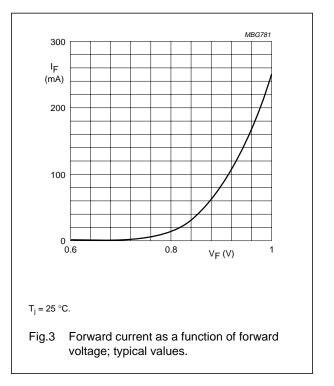
SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th(j-tp)</sub>	thermal resistance from junction to tie-point		15	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	note 1	125	K/W

#### Note

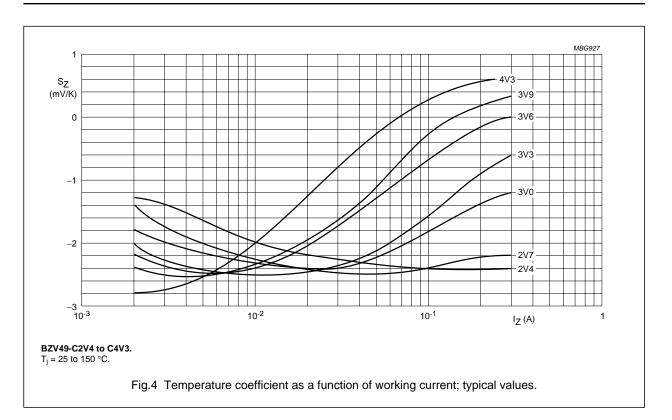
1. Device mounted on a ceramic substrate; area =  $2.5 \text{ cm}^2$ ; thickness = 0.7 mm.

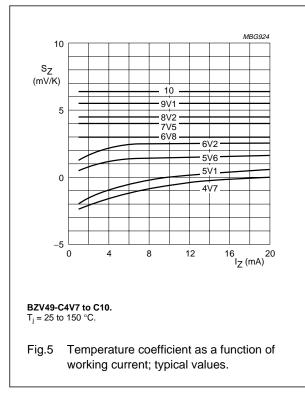
#### **GRAPHICAL DATA**





## BZV49 series

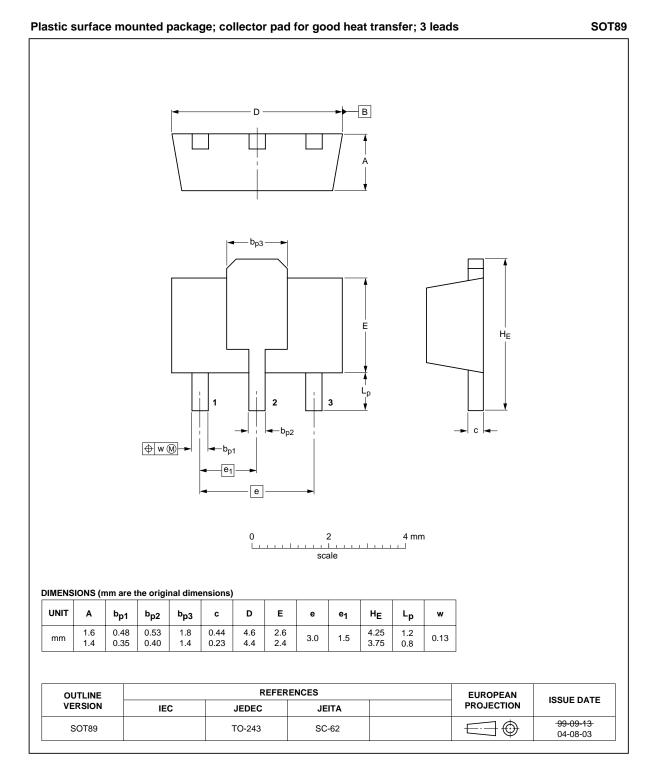




2005 Feb 03

## **BZV49** series

#### PACKAGE OUTLINE



2005 Feb 03

### **BZV49** series

#### DATA SHEET STATUS

LEVEL	DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)(3)</sup>	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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Printed in The Netherlands R7

6 R76/04/pp10

Date of release: 2005 Feb 03

Document order number: 9397 750 13926

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